

E1 process chamber at a temperature greater than about 450 °C, said steam provided in a ratio of at least 0.005 relative to other gases present in the rapid thermal process chamber.

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Please add claim 43 below.

Sub F4 E2 43. (New) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to form part of a gate of a transistor; and

subjecting the dielectric film to a wet oxidation with steam provided by heating a mixture of hydrogen and oxygen gases in a rapid thermal process chamber at a temperature greater than about 450 °C, said mixture is a ratio from approximately 0.1 to approximately 0.80 of hydrogen gas to oxygen gas, wherein said steam is provided in a ratio of at least 0.005 relative to other gases present in the rapid thermal process chamber.

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